

# Thyristor

$$V_{RRM} = 1600 \text{ V}$$

$$I_{TAV} = 80 \text{ A}$$

$$V_T = 1.43 \text{ V}$$

## Single Thyristor

Part number

**CMA80E1600HB**



Backside: anode



### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

### Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

### Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).



Thyristor				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1700	V	
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1600	V	
$I_{RD}$	reverse current, drain current	$V_{R/D} = 1600 V$	$T_{VJ} = 25^{\circ}C$		10	$\mu A$	
		$V_{R/D} = 1600 V$	$T_{VJ} = 125^{\circ}C$		3	mA	
$V_T$	forward voltage drop	$I_T = 80 A$	$T_{VJ} = 25^{\circ}C$		1.47	V	
		$I_T = 160 A$			1.90	V	
		$I_T = 80 A$	$T_{VJ} = 125^{\circ}C$		1.43	V	
		$I_T = 160 A$			1.93	V	
$I_{TAV}$	average forward current	$T_C = 115^{\circ}C$	$T_{VJ} = 150^{\circ}C$		80	A	
$I_{T(RMS)}$	RMS forward current	180° sine			126	A	
$V_{T0}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		0.90	V	
$r_T$	slope resistance				6.4	m $\Omega$	
$R_{thJC}$	thermal resistance junction to case				0.2	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.25		K/W	
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		620	W	
$I_{TSM}$	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		720	A	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		780	A	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		610	A	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		660	A	
$I^2t$	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		2.59	kA <sup>2</sup> s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		2.53	kA <sup>2</sup> s	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		1.86	kA <sup>2</sup> s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		1.81	kA <sup>2</sup> s	
$C_J$	junction capacitance	$V_R = 400 V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		32	pF	
$P_{GM}$	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 150^{\circ}C$		10	W	
		$t_p = 300 \mu s$			5	W	
$P_{GAV}$	average gate power dissipation				0.5	W	
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^{\circ}C; f = 50 \text{ Hz}$	repetitive, $I_T = 240 A$		150	A/ $\mu s$	
		$t_p = 200 \mu s; di_G/dt = 0.3 A/\mu s;$ $I_G = 0.45 A; V = \frac{2}{3} V_{DRM}$	non-repet., $I_T = 80 A$		500	A/ $\mu s$	
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty; \text{ method 1 (linear voltage rise)}$	$T_{VJ} = 125^{\circ}C$		1000	V/ $\mu s$	
$V_{GT}$	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		1.4	V	
			$T_{VJ} = -40^{\circ}C$		1.6	V	
$I_{GT}$	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		80	mA	
			$T_{VJ} = -40^{\circ}C$		200	mA	
$V_{GD}$	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$		0.2	V	
$I_{GD}$	gate non-trigger current				5	mA	
$I_L$	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		450	mA	
		$I_G = 0.3 A; di_G/dt = 0.3 A/\mu s$					
$I_H$	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		100	mA	
$t_{gd}$	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	$\mu s$	
		$I_G = 0.5 A; di_G/dt = 0.5 A/\mu s$					
$t_q$	turn-off time	$V_R = 100 V; I_T = 80 A; V = \frac{2}{3} V_{DRM}$ $di/dt = 15 A/\mu s \quad dv/dt = 20 V/\mu s \quad t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$		150	$\mu s$	



Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			70	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		150	°C
<b>Weight</b>				6		g
$M_D$	mounting torque		0.8		1.2	Nm
$F_C$	mounting force with clip		20		120	N

**Product Marking**



**Part description**

- C = Thyristor (SCR)
- M = Thyristor
- A = (up to 1800V)
- 80 = Current Rating [A]
- E = Single Thyristor
- 1600 = Reverse Voltage [V]
- HB = TO-247AD (3)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CMA80E1600HB	CMA80E1600HB	Tube	30	513206

**Equivalent Circuits for Simulation**

*\* on die level*

$T_{VJ} = 150^{\circ}C$



**Thyristor**

$V_{0\ max}$	threshold voltage	0.9	V
$R_{0\ max}$	slope resistance *	3.9	mΩ



**Outlines TO-247**



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.215 BSC		5.46 BSC	
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212		5.38	
S	0.242 BSC		6.14 BSC	
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39



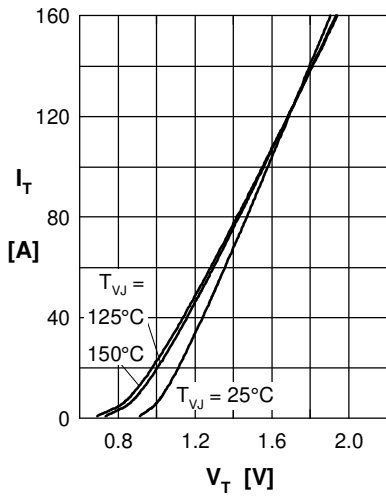
**Thyristor**


Fig. 1 Forward characteristics

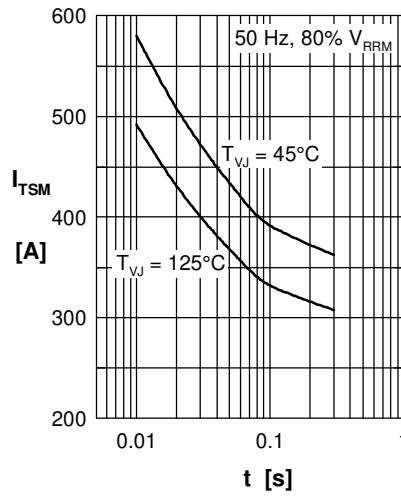
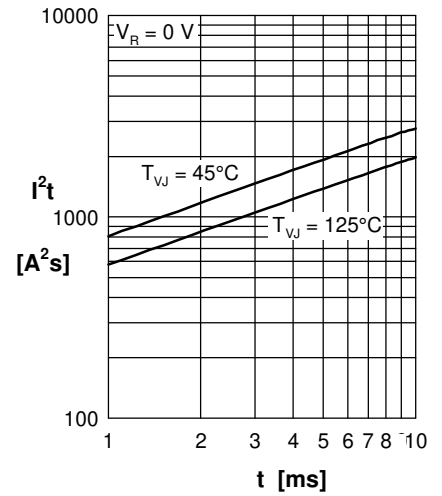
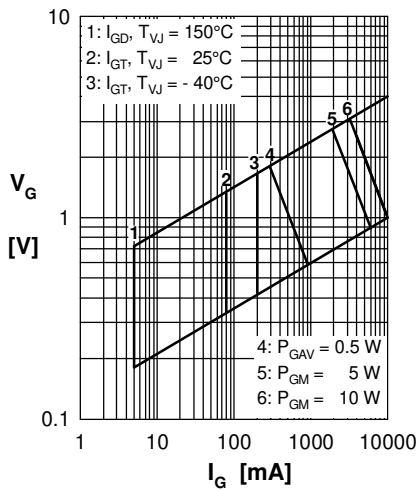

 Fig. 2 Surge overload current  
 $I_{TSM}$ : crest value,  $t$ : duration

 Fig. 3  $I^2t$  versus time (1-10 s)


Fig. 4 Gate voltage &amp; gate current

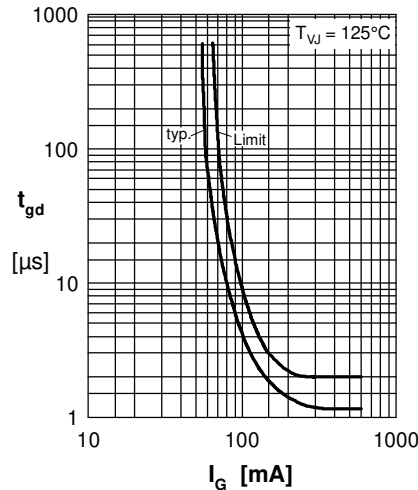
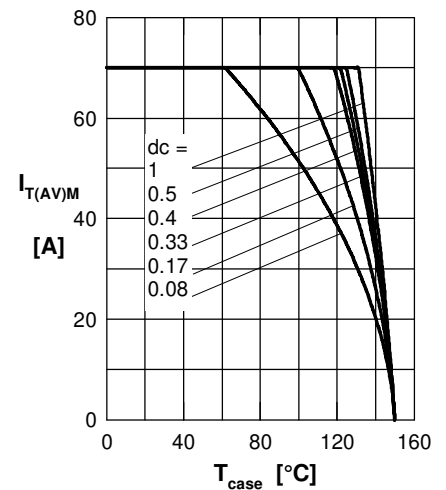

 Fig. 5 Gate controlled delay time  $t_{gd}$ 


Fig. 6 Max. forward current at case temperature

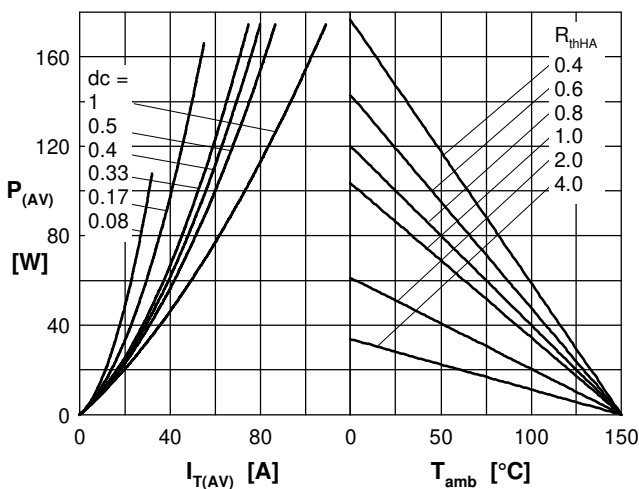
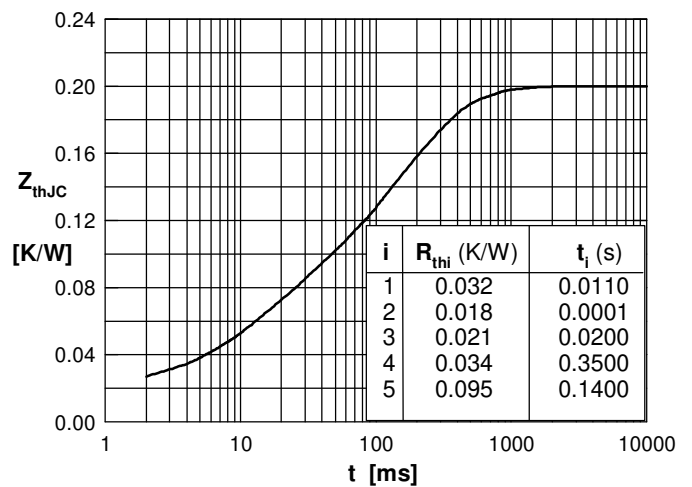

 Fig. 7a Power dissipation versus direct output current  
 Fig. 7b and ambient temperature


Fig. 7 Transient thermal impedance junction to case

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [SCRs category](#):*

*Click to view products by [IXYS manufacturer](#):*

Other Similar products are found below :

[NTE5428](#) [T1500N16TOF VT](#) [TT162N16KOF-A](#) [TT162N16KOF-K](#) [TT330N16AOF](#) [VS-22RIA20](#) [VS-2N685](#) [057219R](#) [T1190N16TOF VT](#)  
[T1220N22TOF VT](#) [T201N70TOH](#) [T700N22TOF](#) [T830N18TOF](#) [TT250N12KOF-K](#) [VS-16RIA120](#) [VS-110RKI40](#) [NTE5427](#) [NTE5442](#)  
[TT251N16KOF-K](#) [VS-22RIA100](#) [VS-16RIA40](#) [TD250N16KOF-A](#) [VS-ST110S16P0](#) [T930N36TOF VT](#) [T2160N24TOF VT](#) [T1190N18TOF](#)  
[VT](#) [T1590N28TOF VT](#) [2N1776A](#) [T590N14TOF](#) [NTE5375](#) [NTE5460](#) [NTE5481](#) [NTE5512](#) [NTE5514](#) [NTE5518](#) [NTE5519](#) [NTE5529](#)  
[NTE5553](#) [NTE5555](#) [NTE5557](#) [NTE5567](#) [NTE5570](#) [NTE5572](#) [NTE5574](#) [NTE5576](#) [NTE5578](#) [NTE5579](#) [NTE5589](#) [NTE5592](#) [NTE5598](#)